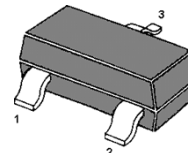


MMBTSB1198 PNP Silicon Epitaxial Planar Transistor

Low frequency transistor

The transistor is subdivided into two groups Q and R, according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	80	V
Collector Emitter Voltage	$-V_{CEO}$	80	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	0.5	A
Collector Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

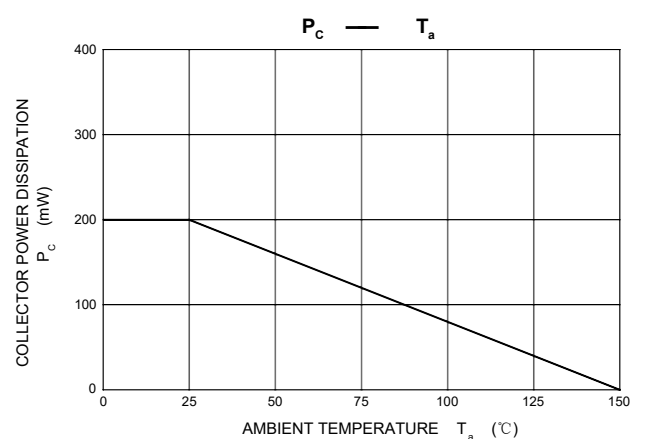
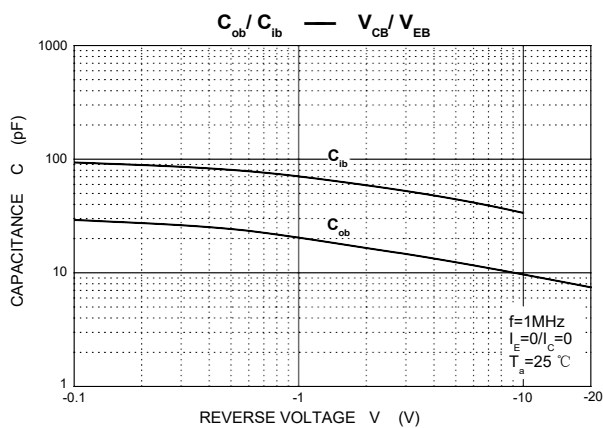
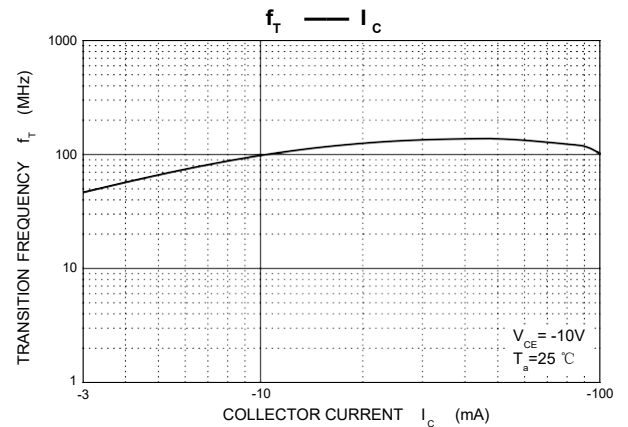
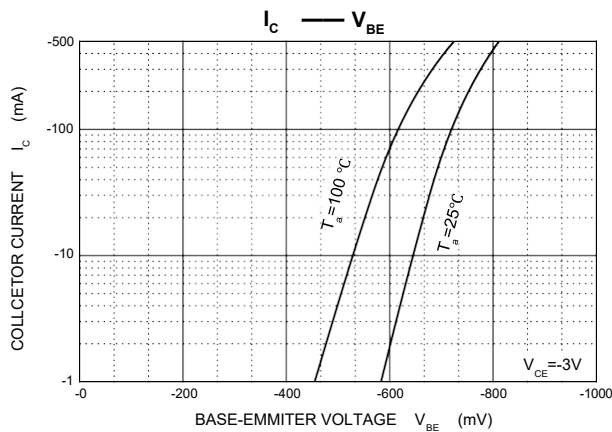
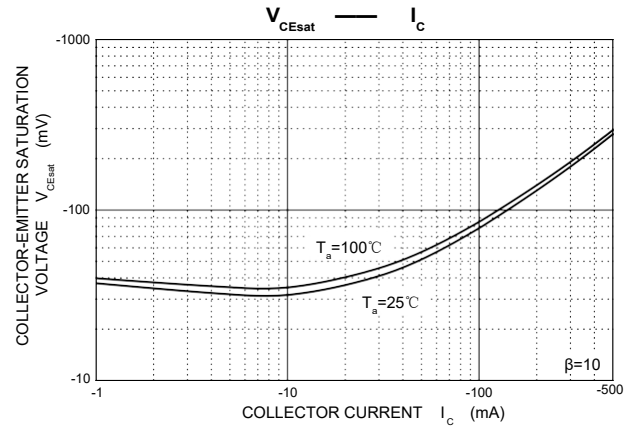
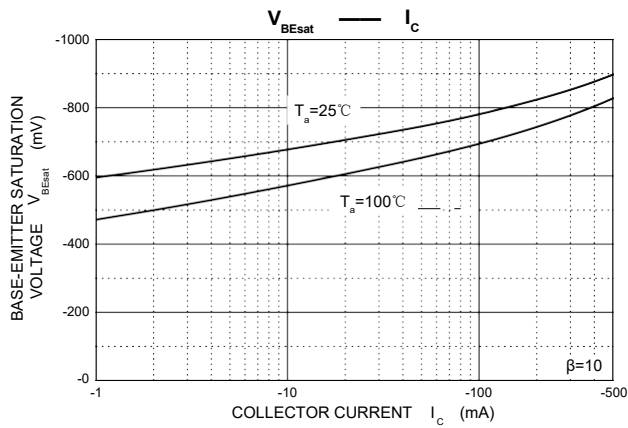
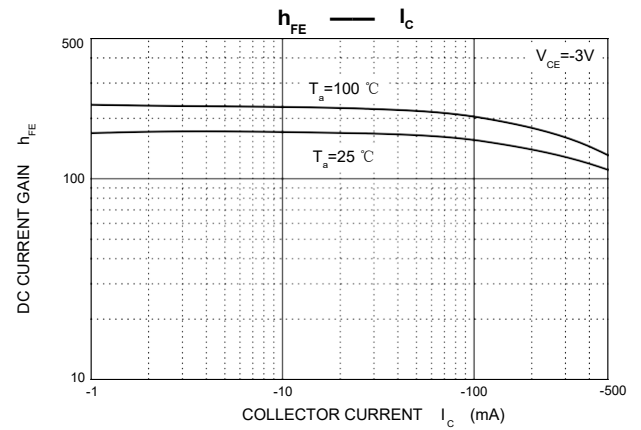
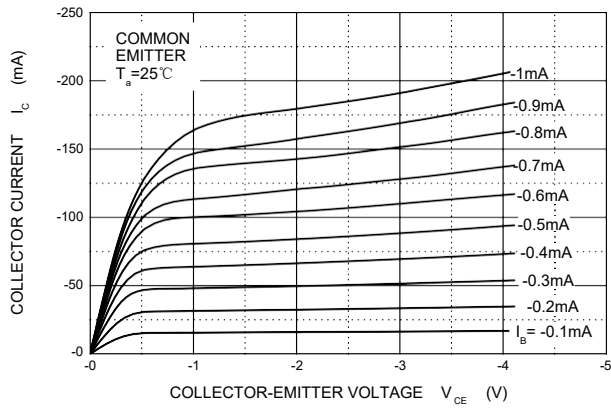
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}$, $I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-2\text{mA}$, $I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}$, $I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$			-0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-3\text{V}$, $I_C=-100\text{mA}$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-10\text{V}$, $I_C=-50\text{mA}$, $f=100\text{MHz}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$		11		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R
Range	120-270	180-390
MARKING	AKQ	AKR

Typical Characteristics

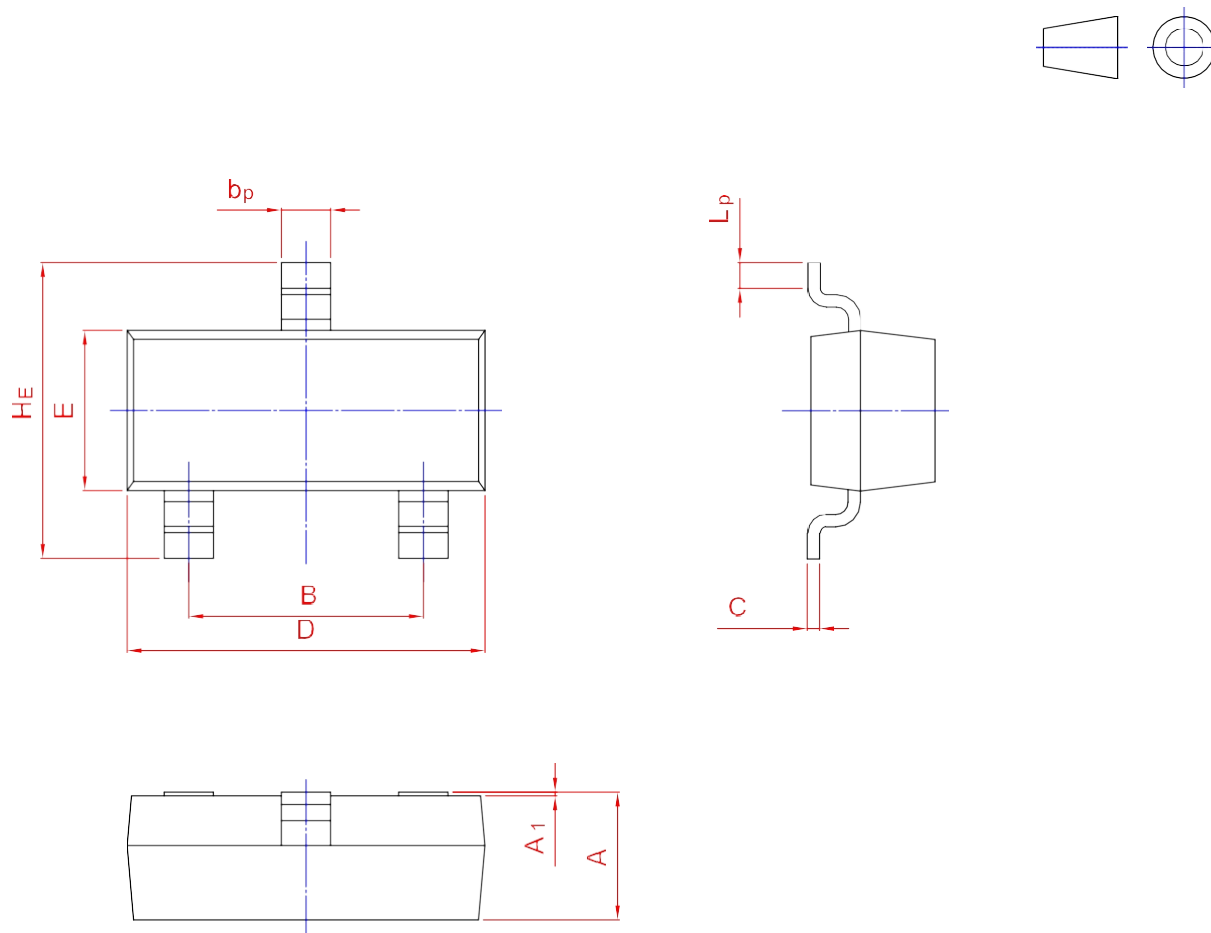
Static Characteristic



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20